Please **amend** claims 1, 2 and 9, as follows:

Sub C1

1. **(Amended)** A thin-film transistor comprising:

a glass substrate; and

formed at an upper part of said glass substrate, a channel region, a source region, a drain region, a first insulating layer and a second insulating layer, wherein:

said channel region, said source region and said drain region comprise polycrystalline silicon,

said glass substrate is such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute,

said first insulating layer covers said channel region, and

said second insulating layer is formed on a surface of said first insulating layer.

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2. **(Amended)** The thin-film transistor according to claim 1, wherein said first insulating layer has a layer thickness whose lower limit is 4nm.

Sub C2

9. **(Amended)** A thin-film transistor comprising:

a glass substrate; and

formed at an upper part of said glass substrate, a channel region, a source region, a drain region and an insulating layer, wherein:

said channel region, said source region and said drain region comprise polycrystalline silicon,

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C2

B19 cont

said glass substrate is such that its compaction is 30 ppm or higher, when said glass substrate is heated at 600° C for 1 hour and thereafter cooled at a rate of 1° C/minute, and

said insulating layer covers said channel region.

Please **add** new claim 22, as follows:

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22. The thin-film transistor according to claim 1, wherein said first insulating layer is a silicon oxide layer or a silicon oxynitride layer.

IN THE ABSTRACT:

Please **replace** the Abstract with the amended Abstract in the following clean page: